EE3230 Lecture 4: Circuit Characterization and Performance Estimation I

Ping-Hsuan Hsieh (謝秉璇)

Delta Building R908 EXT 42590 phsieh@ee.nthu.edu.tw

Outline

Delay estimation

- Logical effort and transistor sizing
- Power dissipation
- Interconnect
- Wire engineering
- Design margin
- Reliability
- Scaling

Transient Response

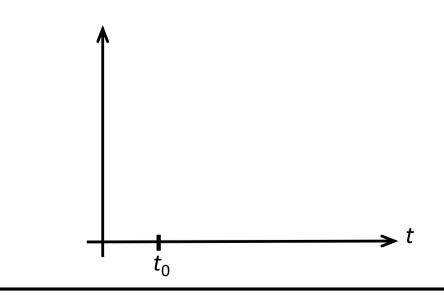
- **DC** analysis tells us V_{out} if V_{in} is constant
- Transient analysis tells us V_{out}(t) with certain V_{in}(t)
 - Requires solving differential equations
- Input is usually considered to be a step or ramp
 - From 0 to V_{DD} or vice versa

Inverter Step Response

• With load capacitance of C_{load}

 $V_{in}(t) = u(t-t_0)V_{DD}$

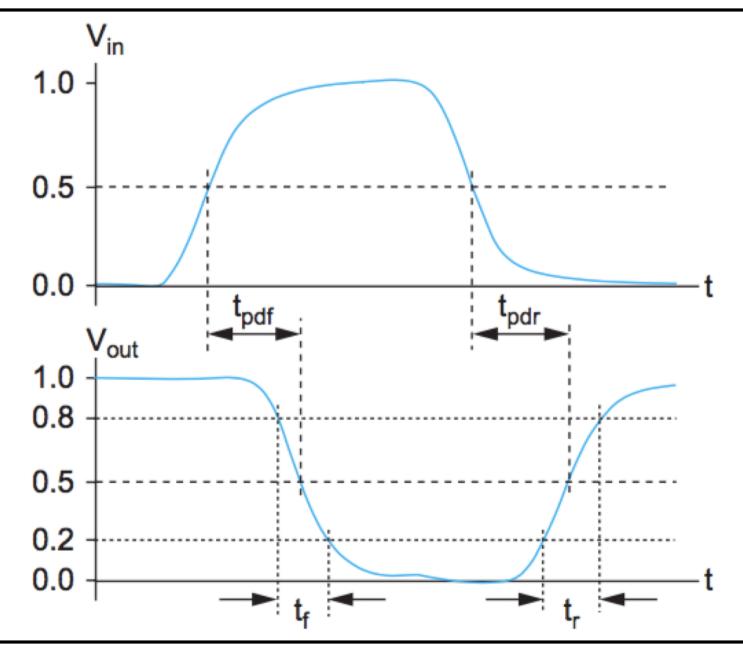
• Current discharging the cap



Delay Definitions (I)

- *t*_{pdr} maximum rising propagation delay
 - From input to rising output crossing $V_{DD}/2$
- *t*_{pdf} maximum falling propagation delay
 - From input to falling output crossing $V_{\text{DD}}/2$
- t_{pd} average propagation delay
 - $t_{pd} = (t_{pdr} + t_{pdf})/2$
- **t**_r rise time
 - For output to go from 0.2 V_{DD} to 0.8 V_{DD}
- **t**_f fall time
 - For output to go from 0.8 V_{DD} to 0.2 V_{DD}

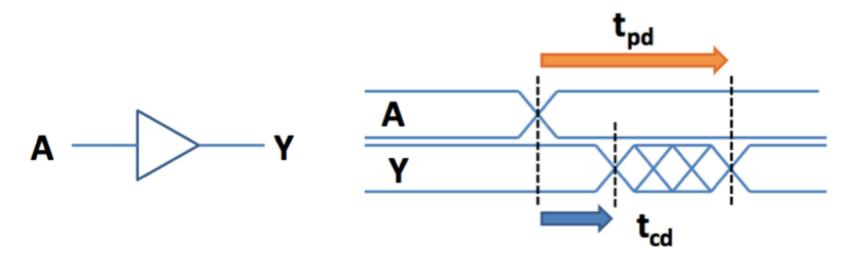
Delay Definitions (II)



Delay Definitions (III)

- t_{cdr} minimum rising contamination delay
 - From input to rising output crossing $V_{DD}/2$
- *t*_{cdf} maximum falling contamination delay
 - From input to falling output crossing $V_{\text{DD}}/2$
- *t*_{cd} average contamination delay

$$- t_{cd} = (t_{cdr} + t_{cdf})/2$$



Delay Estimation (I)

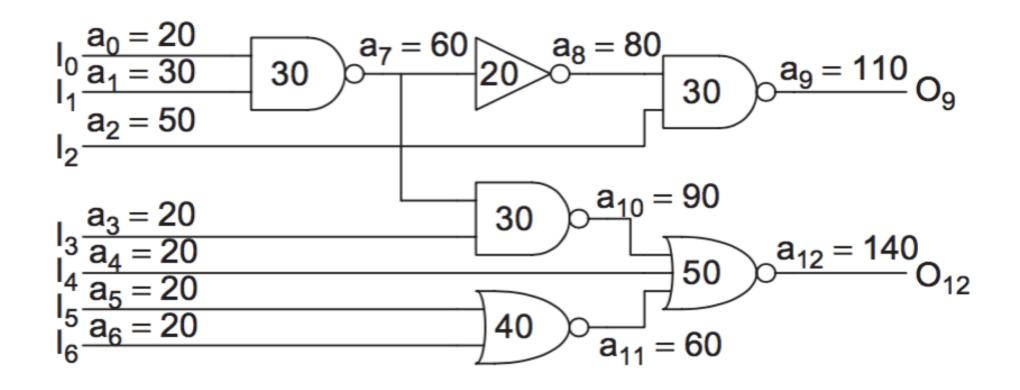
- Estimate delay easily
 - Not as accurate as simulations
 - Easier to ask "what if?"
- Step response looks like a 1st order RC response (decaying exponential)
- Use RC delay models
 - C = total capacitance on output node
 - Use effective R
 - $t_{pd} = RC$
- \rightarrow Characterize transistors by finding their effective **R**
 - Depend on average current of gate switches

Delay Estimation (II)

Critical path

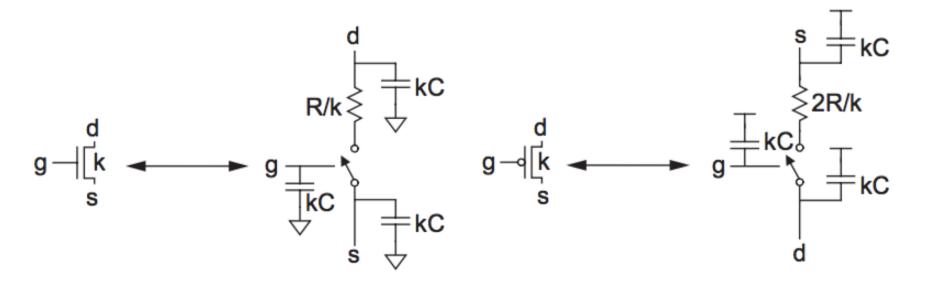
- The signal path with the slowest (most critical) timing
- Affected at 4 different levels
- Architecture/micro-architecture levels
 - Tradeoff of pipeline stages, number of execution units, and size of memory. It's the level that impacts the most.
- Logic level
 - Tradeoff of functional block types, number of gate in the cycle, fan-in and fan-out number
- Circuit level
 - Transistor size and logic styles/families
- Layout level
 - Floor-plan, wire length, and parasitics

Critical Path

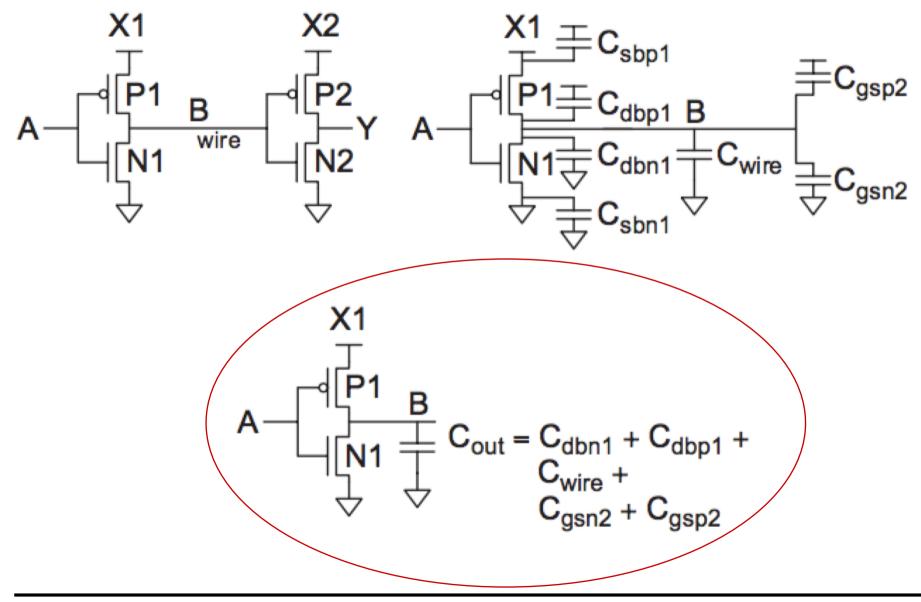


RC Delay Models

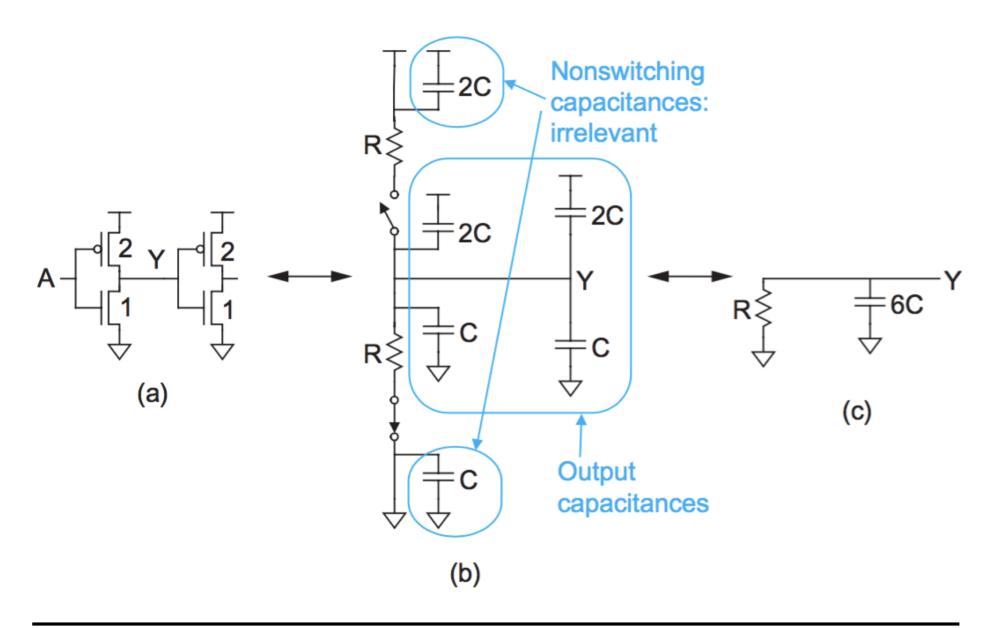
- Equivalent circuit for MOS transistors
 - Ideal switch + capacitance and ON resistance
 - Unit NMOS has resistance R and capacitance C
 - Unit PMOS has resistance 2R and capacitance C
- Capacitance proportional to width
- Resistance inversely proportional to width



Example: Inverter



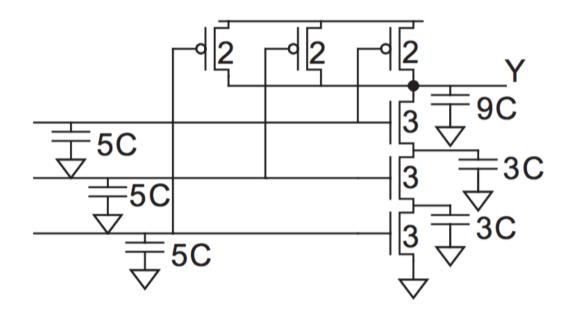
Example: Inverter



Example: NAND3

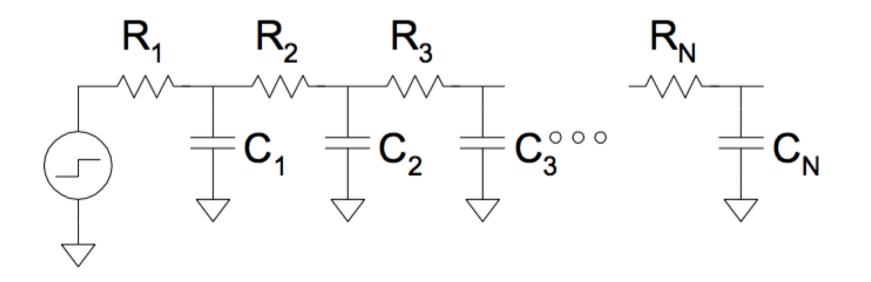
- Sketch a 3-input NAND with transistor widths chosen to achieve effective rise and fall resistances equal to a unit inverter (R)
- Annotate the 3-input NAND gate with gate and diffusion capacitance

Delay of NAND3



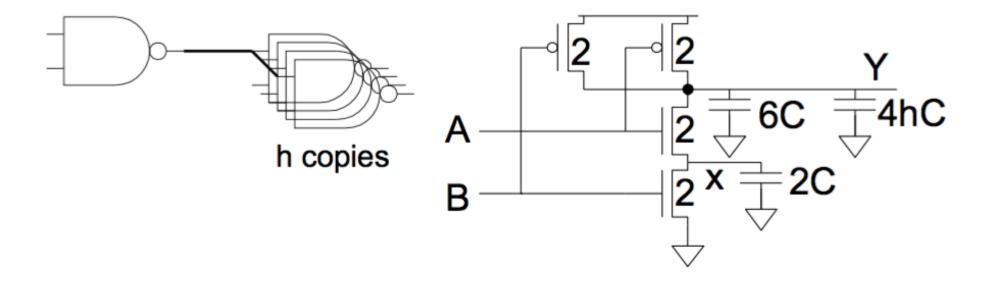
Elmore Delay Model

- Pull-up or pull-down network can be modeled as RC ladder
- Elmore delay model of an RC ladder



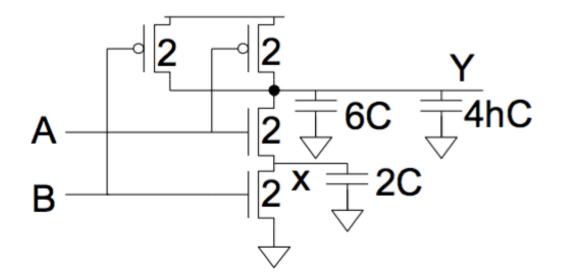
Example: 2-Input NAND

 Estimate worst-case rising and falling delays of 2-input NAND driving *h* identical gates



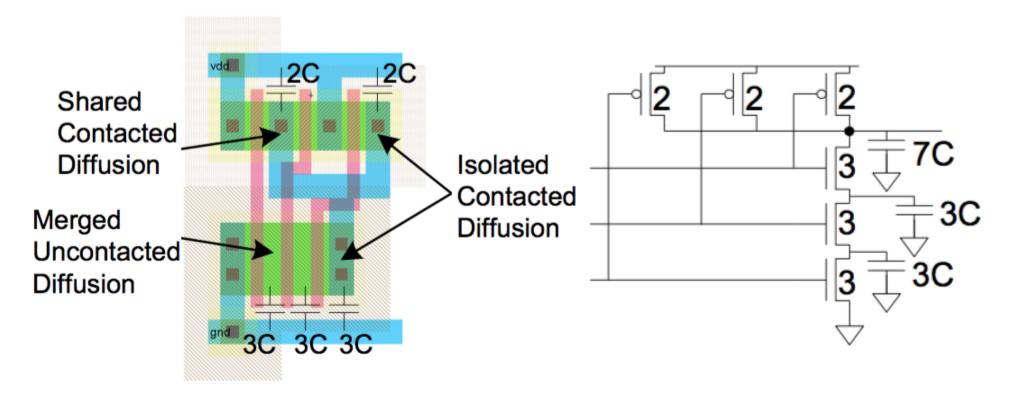
Contamination Delay

- Best-case (contamination) delay can be substantially less than worst-case delay
- Example: If both inputs fall simultaneously

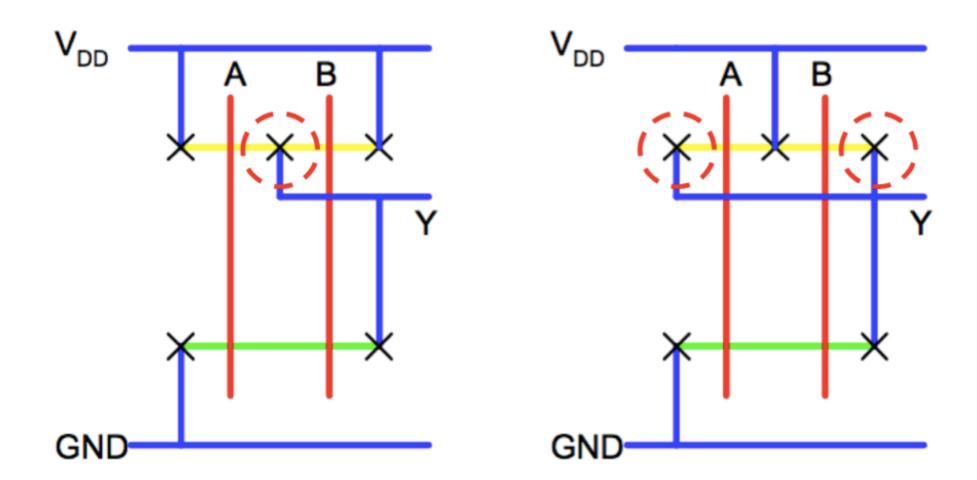


Diffusion Capacitance

- Good layout minimizes diffusion area
- Example: NAND3
 - Sharing diffusion contacts reduces output cap by 2C
 - Merged un-contacted diffusion might help too



Layout Comparison



Delay Components

- Parasitic delay
 - Independent of load
- Effort delay
 - Proportional to load capacitance

Outline

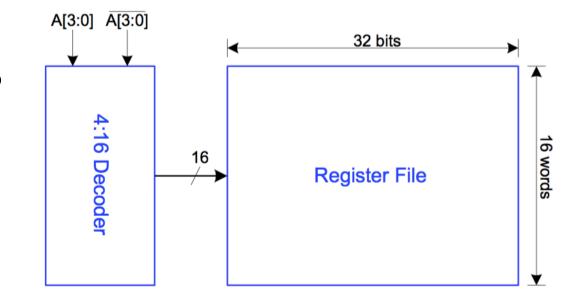
- Delay estimation
- Logical effort and transistor sizing
- Power dissipation
- Interconnect
- Wire engineering
- Design margin
- Reliability
- Scaling

Introduction

- Chip designers face a bewildering array of choices
 - What is the best circuit topology for a given function?
 - How many stages of logic gives the least delay?
 - How wide should the transistors be?
- Logical effort is a method to make these decisions
 - Uses a simple model of delay
 - Allows back-of-the-envelope calculations
 - Helps make rapid comparison between alternatives
 - Emphasizes remarkable symmetries

Example: Decoder for a Register File

- Specifications
 - 16-word register file
 - Each word is 32-bit wide
 - Each bit presents a load of 3 unit-sized transistors
 - True and complementary address inputs A[3:0]
 - Each input may drive 10 unit-sized transistors
- Need to decide:
 - How many stages?
 - How large should each gate be?
 - How fast can the decoder operate?



• Express delays in **process-independent** unit

• Express delays in process-independent unit

$$d = d_{abs}/\tau$$

• Delay has two components

• Express delays in process-independent unit

 $d = d_{abs}/\tau$

• Delay has two components

d = f + p

• Effort delay (or stage effort) has two components

• Express delays in process-independent unit

 $d = d_{abs}/\tau$

• Delay has two components

d = f + p

• Effort delay (or stage effort) has two components

f = gh

- g: logical effort
 - Measure relative ability of date to deliver current
 - -g = 1 for inverter

• Express delays in process-independent unit

 $d = d_{abs}/\tau$

• Delay has two components

d = f + p

• Effort delay (or stage effort) has two components

f = gh

- *h*: electrical effort
 - Ratio of output to input capacitance
 - Sometimes called fanout

• Express delays in process-independent unit

 $d = d_{abs}/\tau$

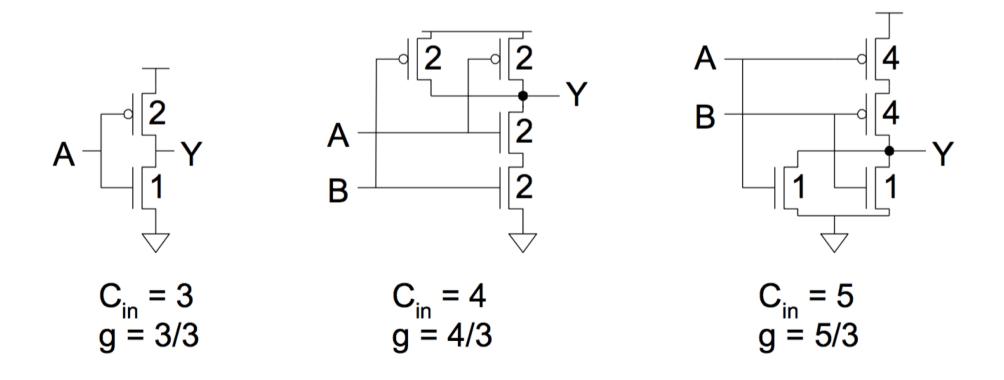
• Delay has two components

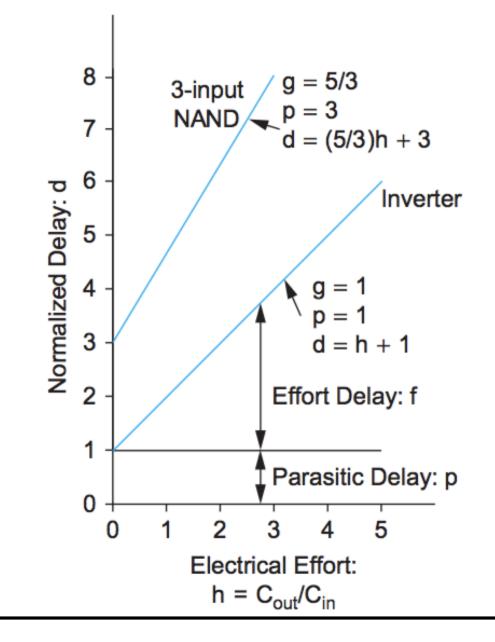
d = f + p

- Parasitic delay **p**
 - Delay of gate driving no load
 - Due to internal parasitic capacitance

Computing Logical Effort

Ratio of input capacitance of a gate to that of an inverter delivering the same output current
 Method #1: Measure from delay vs. fanout plots
 Method #2: Estimate by counting transistor widths





• Logic effort of common gates

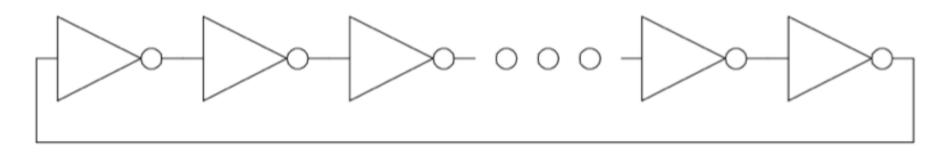
Gate Type	Number of inputs					
	1	2	3	4	n	
Inverter	1					
NAND		4/3	5/3	6/3	(n+2)/3	
NOR		5/3	7/3	9/3	(2n+1)/3	
Tri-state, MUX	2	2	2	2	2	
XOR, XNOR		4, 4	4, 12, 6	8, 16, 16, 8		

• Parasitic delay of common gates

Gate Type	Number of inputs					
	1	2	3	4	n	
Inverter	1					
NAND		2	3	4	n	
NOR		2	3	4	n	
Tri-state, MUX	2	4	6	8	2n	
XOR, XNOR		4	6	8		

N-stage Ring Oscillator

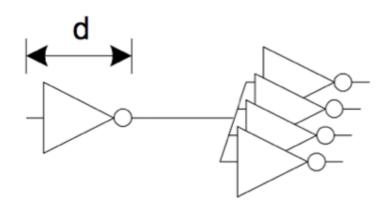
• Estimate the frequency



- Logic effort:
- Electrical effort:
- Parasitic delay:
- Stage delay:
- Frequency:

Example: FO-4 Inverter

• Estimate the delay of an inverter with fanout of 4 (FO4)



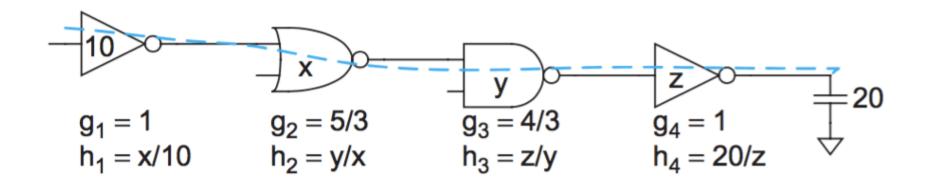
- Logic effort:
- Electrical effort:
- Parasitic delay:
- Stage delay:
- Rule of thumb: FO4 delay for a process is 1/3 to 1/2 of the minimum channel length. EX 180 nm: FO4 =60~90 ps
- Highly sensitive to process, voltage, & temperature variations

Multistage Logic Networks

- Logic effort generalizes to multistage networks
- Path logical effort $G = \prod g_i$
- Path electrical effort

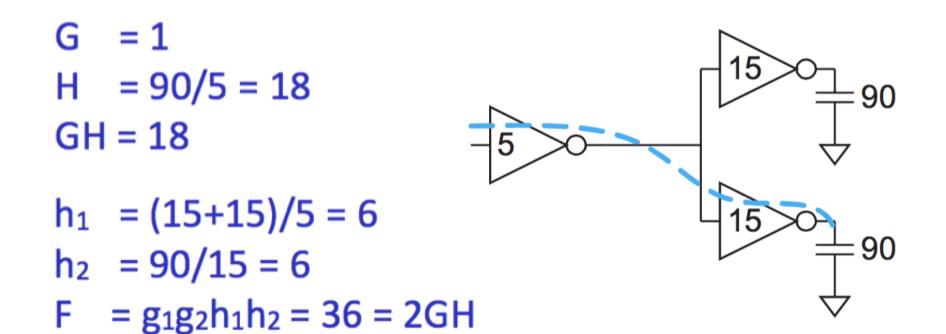
$$H = C_{out-path} / C_{in-path}$$

• Path effort $F = \prod f_i = \prod g_i h_i$



Paths with Branches

- F = GH?
- No! Consider paths with branches



Branching Effort

• Account for branches in path

- Branching effort
$$b = \frac{C_{\text{on path}} + C_{\text{off path}}}{C_{\text{on path}}}$$

- Path branching effort $B = \prod b_i$

• Now we can compute path effort

$$F = GBH$$

• Path effort delay

 $D_F = \sum f_i$

• Path parasitic delay

 $P = \sum p_i$

• Path delay

$$D = \sum d_i = D_F + P$$

$$D = \sum d_i = D_F + P$$

Delay is the smallest when each stage bears the same effort

 $\hat{f} = g_i h_i = F^{\frac{1}{N}}$

• Minimum delay of N-stage path is

 $D = NF^{\frac{1}{N}} + P$

- This is the **key** result of logic effort analysis
 - Find fastest possible delay
 - Doesn't require calculating gate size

Gate Size

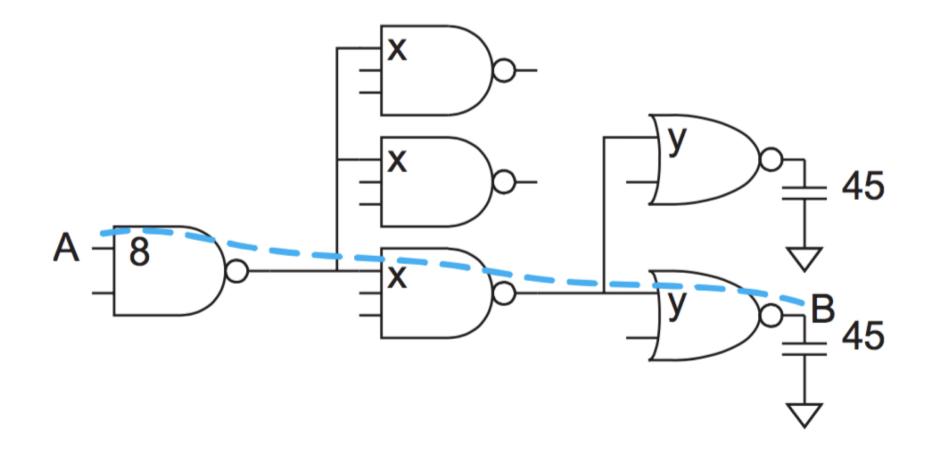
• How wide should the gates be for the least delay?

$$\hat{f} = gh = g \frac{C_{out}}{C_{in}}$$
$$\Rightarrow C_{in_i} = \frac{g_i C_{out_i}}{\hat{f}}$$

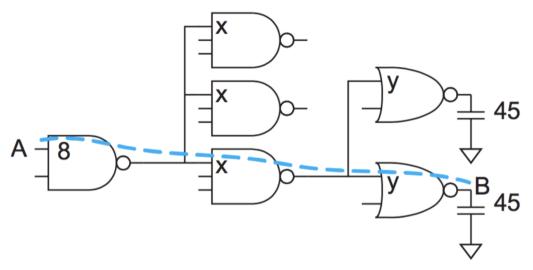
- Working backwards, apply capacitance transformation to find input capacitance of each gate with given load it drives
- Check work by verifying input cap spec is met

Example: 3-Stage Path

• Select gate size x and y that minimize the delay from A to B



Example: 3-Stage Path



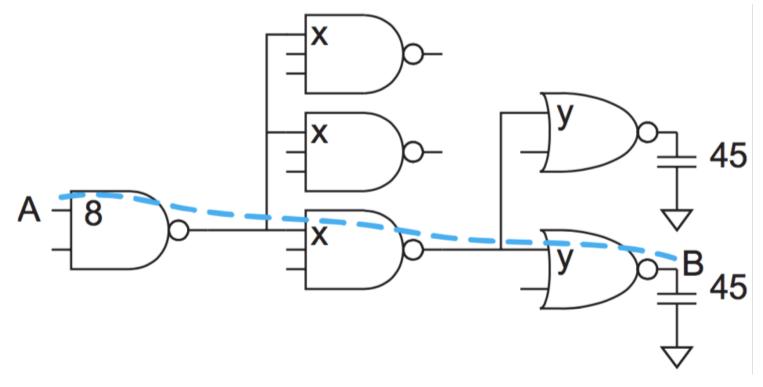
- Logical effort G = (4/3)(5/3)(5/3) = 100/27
- Electrical effort
- Branching effort
- Path effort F = GBH
- Best stage effort
- Parasitic delay P = 2 + 3 + 2 = 7
- Delay

Example: 3-Stage Path

• Work backwards for sizes

$$-y = 45*(5/3)/5 = 15$$

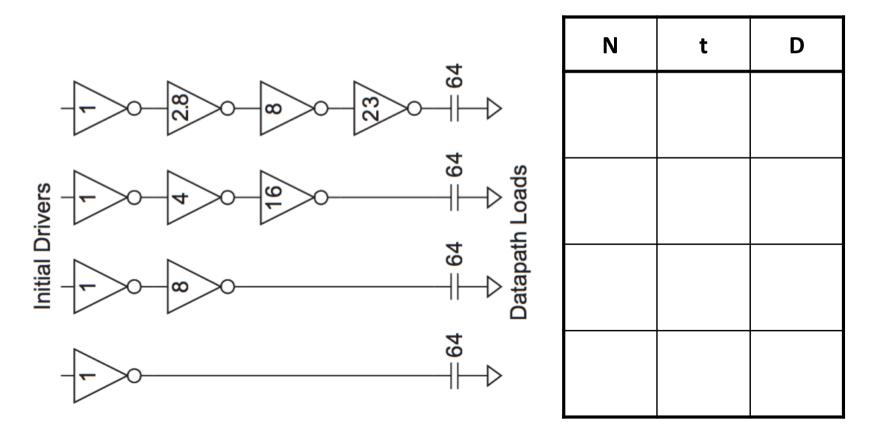
$$-x = (15*2)*(5/3)/5 = 10$$



• What about NMOS and PMOS sizes in each gate?

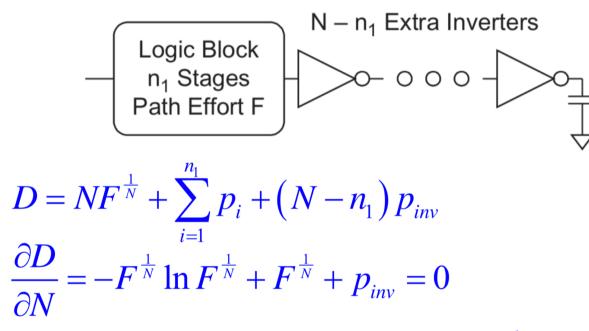
Best Number of Stages

- How many stages should a path use
 - Minimizing number of stages is not always the fastest
- Example: Drive 64-bit datapath with unit inverter



Derivation

- Consider inserting inverters into the signal chain
 - How many stages give the least delay?



• Define the best stage effort $\rho = F^{\frac{1}{N}}$

 $p_{inv} + \rho (1 - \ln \rho) = 0$

Best Stage Effort

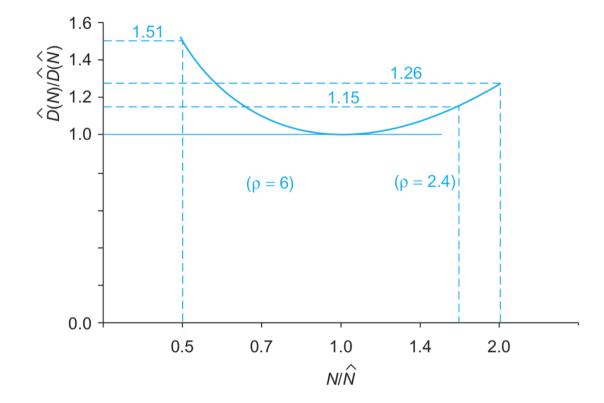
- $p_{inv} + \rho (1 \ln \rho) = 0$ has no closed-form solution
- Neglecting parasitics ($p_{inv} = 0$), we define

ho = 2.718 (e)

• For p_{inv} = 1, solve numerically for ρ = 3.59

Sensitivity Analysis

• How sensitive is the delay to the number of stages near the best number?



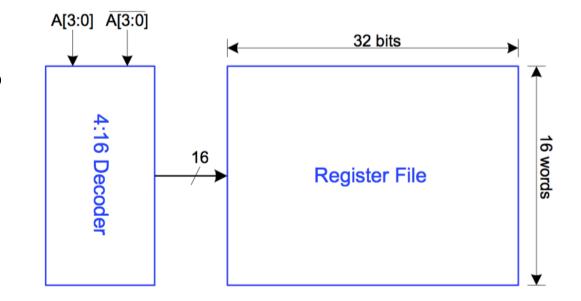
- 2.4 < ρ < 6 gives delay with 15% variations
 - 4 is a common choice

Example: Decoder for a Register File

• Specifications

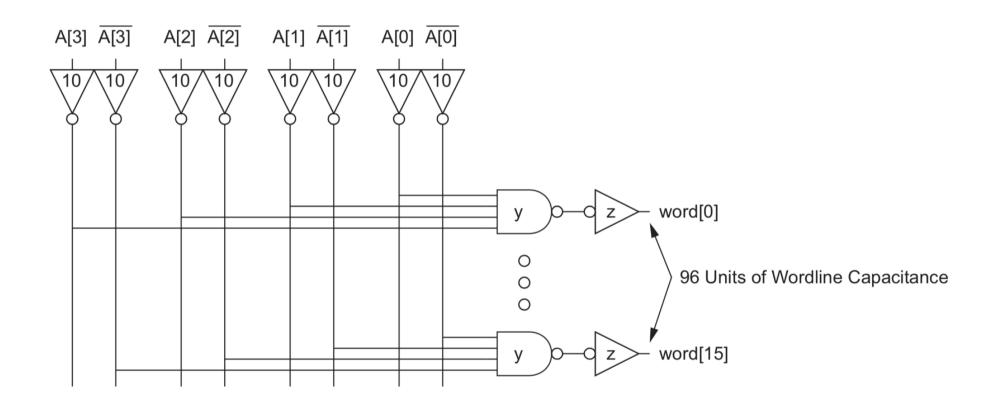
(revisited)

- 16-word register file
- Each word is 32-bit wide
- Each bit presents a load of 3 unit-sized transistors
- True and complementary address inputs A[3:0]
- Each input may drive 10 unit-sized transistors
- Need to decide:
 - How many stages?
 - How large should each gate be?
 - How fast can the decoder operate?



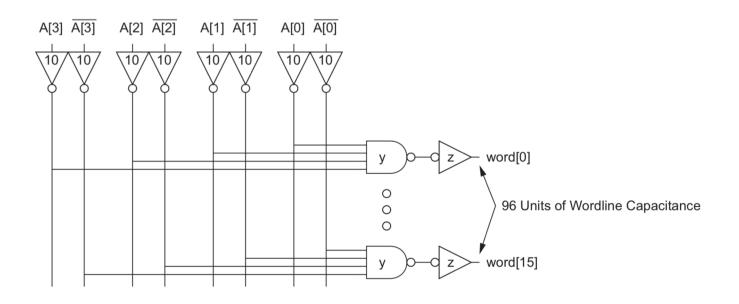
Number of Stages

- Decoder effort is mainly electrical and branching
 Electrical effort H =
 Branching effort B =
- If we neglect logical effort (by assuming G = 1)
 Path effort F =
 Number of stages N =



Gate Sizes and Delay

- Logical effort G =
- Path effort F =
- Stage effort $\hat{f} =$
- Path delay D =
- Gate sizes z = y =



• Different alternatives

Design	N	G	Р	D
NAND4-INV	2	2	5	29.8
NAND2-NOR2	2	20/9	4	30.1
INV-NAND4-INV	3	2	6	22.1
NAND4-INV-INV-INV	4	2	7	21.1
NAND2-NOR2-INV-INV	4	20/9	6	20.5
NAND2-INV-NAND2-INV	4	16/9	6	19.7
INV-NAND2-INV-NAND2-INV	5	16/9	7	20.4
NAND2-INV-NAND2-INV-INV-INV	6	16/9	8	21.6

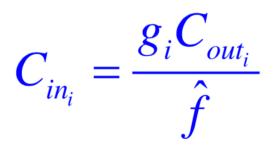
Review

	Stage	Path
Number of stages	1	Ν
Logical effort	g	$G = \prod g_i$
Electrical effort	$h = \frac{C_{out}}{C_{in}}$	$H = \frac{C_{out-path}}{C_{in-path}}$
Branching effort	$b = \frac{(C_{on-path} + C_{off-path})}{C_{on-path}}$	$B = \prod b_i$
Effort	f = gh	F = GBH
Effort delay	f	$D_F = \sum f_i$
Parasitic delay	р	$P = \sum p_i$
Delay	d = f + p	$D = \sum d_i = D_F$

Method of Logical Effort

- 1. Compute path effort F = GBH
- 2. Estimate the best number of stages $N = \log_4 F$
- 3. Sketch path with N stages
- 4. Estimate the least delay
- 5. Determine the best stage effort
- 6. Find gate sizes

$$D = NF^{\frac{1}{N}} + P$$
$$\hat{f} = F^{\frac{1}{N}}$$



Limits of Logical Effort

- Chicken and egg problem
 - Need path to compute G
 - Don't know the number of stages with G
- Simplified delay model
 - Neglect input rise time effects, velocity saturation, body effect, ...
- Neglect interconnect effects
 - Require iterations to take wire capacitance into account
- Maximum speed only
 - Not minimum area/power for constrained delay

Summary

- Logical effort is useful when considering circuit delay
 - Numerical logical effort characterize gates
 - NANDs are faster than NORs in CMOS
 - Paths are fastest when effort delays are ~4
 - Path delay is not very sensitive to stages and sizes
 - Using fewer stages doesn't necessarily give faster result
- Language for discussing fast circuits
 - Practice required to master